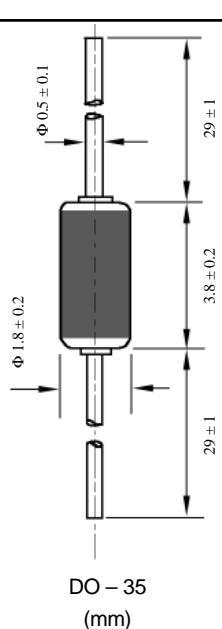


**BI-DIRECTIONAL
TRIGGER DIODES**
DO-35 玻壳封装双向触发二极管
DO-35 GLASS-SEALED BI-DIRECTIONAL TRIGGER DIODES

符号 Symbol	参数 Parameter	测试条件 Test Condition	型号 Type	Min	Typ	Max	Unit	外型尺寸 Package (单位: mm)
V_{BO}	击穿电压 Breakdown Voltage	见图1 See Fig 1	DB-3 DB-4 DB-6	28 35 56	32 40 60	36 45 70	V	
$ +V_{BO} - -V_{BO} $	击穿电压对称性 Breakover Voltage Symmetry	见图1 See Fig 1	DB-3 DB-4 DB-6			3 3 4	V	
$ \pm \Delta V $	动态回弹电压 Dynamic Breakback Voltage	$\Delta I = I_{BO} - I_F - 10\text{mA}$ See Fig 1	DB-3 DB-4 DB-6	5 5 10			V	
V_o	输出电压 Output Voltage	见图2 See Fig 2		5			V	
I_{BO}	击穿电流 Breakdown Current					100	μA	
t_r	上升时间 Rise Time	见图3 See Fig 3			1.5		μs	
I_B	漏电流 Leakage Current	$V_m = 0.5V_{BO}(\text{Max})$ 见图1 See Fig 1				10	μA	

极限参数
LIMITING VALUES

符号 Symbol	参数 Parameter		Value		Unit
P_c	功耗 Power Dissipation	$t_a = 50^\circ\text{C}$	150		mW
I_{Fmax}	峰值脉冲电流 Peak Pulse Current	$t_p = 10\mu\text{s}$	DB-3	2.0	A
		120pps	DB-4	2.0	
		$T_a \leq 40^\circ\text{C}$	DB-6	16	
T_r	贮存与工作结温范围 Storage and Operating Junction Temperatuer Range		40 to 125 40 to 110		°C
T_J					

DO-35 玻壳封装双向触发二极管特性曲线

DO-35 GLASS-SEALED BI-DIRECTIONAL TRIGGER DIODE

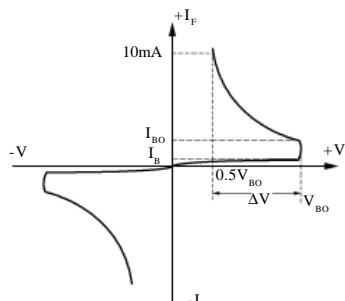


FIG-1 I - V 特性曲线

Current - voltage characteristics

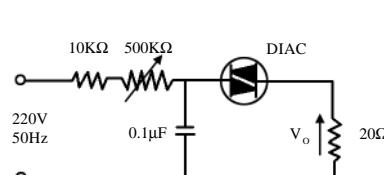


FIG-2 输出电压测试电路

Test circuit for output voltage

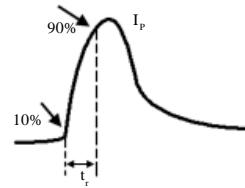


FIG-3 测试电路见图2, 调整 R,
 $I_p=0.5\text{A}$

Test circuit see diagram 2. Adjust
R for $I=0.5\text{A}$

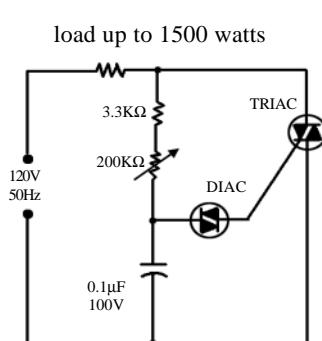


FIG-4 典型 DIAC-TRIAC 全波相控电路
Typical DIAC-TRIAC full-wave Phase control

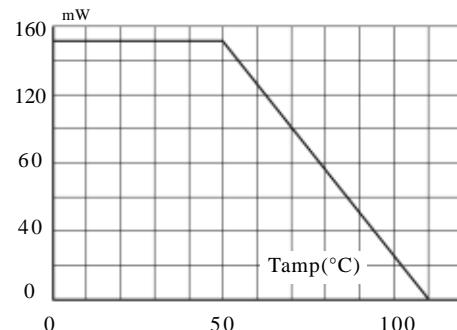


FIG-5 功耗环境温度关系曲线 (最大值)
Power dissipation versus ambient temperature(maximum values)

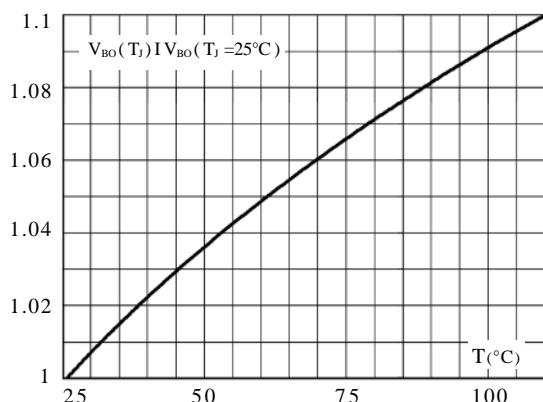


FIG-6 V_{BO} 的相对变化与结温关系曲线 (典型值)
Relative variation of V_{BO} versus junction temperature
(typical values)

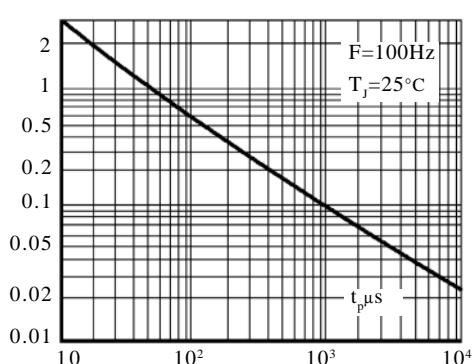


FIG-7 峰值脉冲电流与脉冲宽度关系曲线 (最大值)
Peak pulse Current versus pulse duration
(maximum values)